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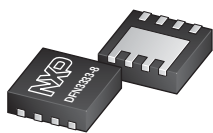
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Kind regards,

Team Nexperia



PSMN9R0-30LL

N-channel DFN3333-8 30 V 9 mΩ logic level MOSFET

Rev. 5 — 13 December 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in DFN3333-8 package qualified to 150 °C. This product is designed and qualified for use in a wide range of industrial, communications and power supply equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources
- Small footprint for compact designs

1.3 Applications

- Battery protection
- Load switching
- DC-to-DC converters
- Power ORing

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1	-	-	21	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	50	W
T_j	junction temperature		-55	-	150	°C

Static characteristics

$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 5\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12	-	10.6	13	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 5\text{ A}$; $T_j = 100\text{ °C}$; see Figure 13	-	-	11.9	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 5\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12	-	8	9	mΩ

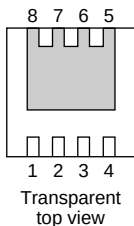
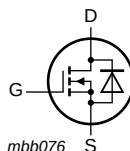


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 10\text{ A}$; $V_{DS} = 15\text{ V}$; see Figure 14 ; see Figure 17	-	2.9	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}$; $I_D = 10\text{ A}$; $V_{DS} = 15\text{ V}$; see Figure 17 ; see Figure 14	-	20.6	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{J(\text{init})} = 25\text{ °C}$; $I_D = 40\text{ A}$; $V_{sup} \leq 30\text{ V}$; unclamped; $R_{GS} = 50\text{ }\Omega$	-	-	32	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>Transparent top view</p>	 <p><i>mbb076</i></p>
2	S	source		
3	S	source		
4	G	gate		
5,6,7,8	D	drain		
mb				
SOT873-1 (DFN3333-8)				

3. Ordering information

Table 3. Ordering information

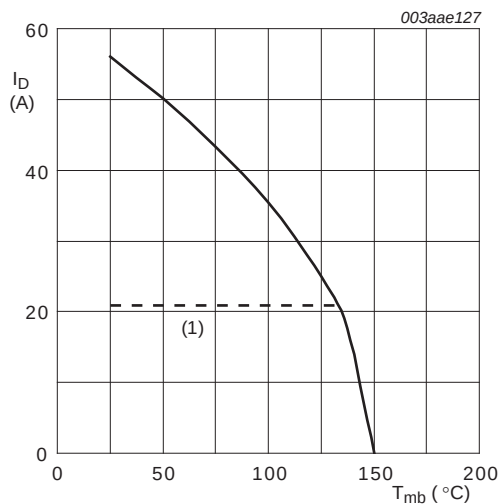
Type number	Package		Version
	Name	Description	
PSMN9R0-30LL	DFN3333-8	plastic thermal enhanced very thin small outline package; no leads; 8 terminals	SOT873-1

4. Limiting values

Table 4. Limiting values

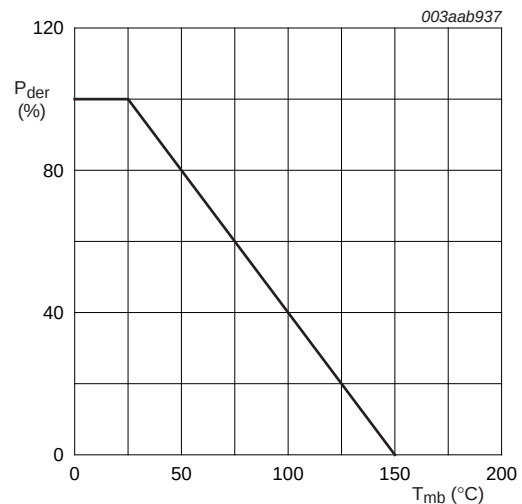
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$T_j \leq 150\text{ °C}$; $T_j \geq 25\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	-	21	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	-	21	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 3	-	226	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	50	W
T_{stg}	storage temperature		-55	150	°C
T_j	junction temperature		-55	150	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	21	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	226	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 40\text{ A}$; $V_{sup} \leq 30\text{ V}$; unclamped; $R_{GS} = 50\text{ }\Omega$	-	32	mJ



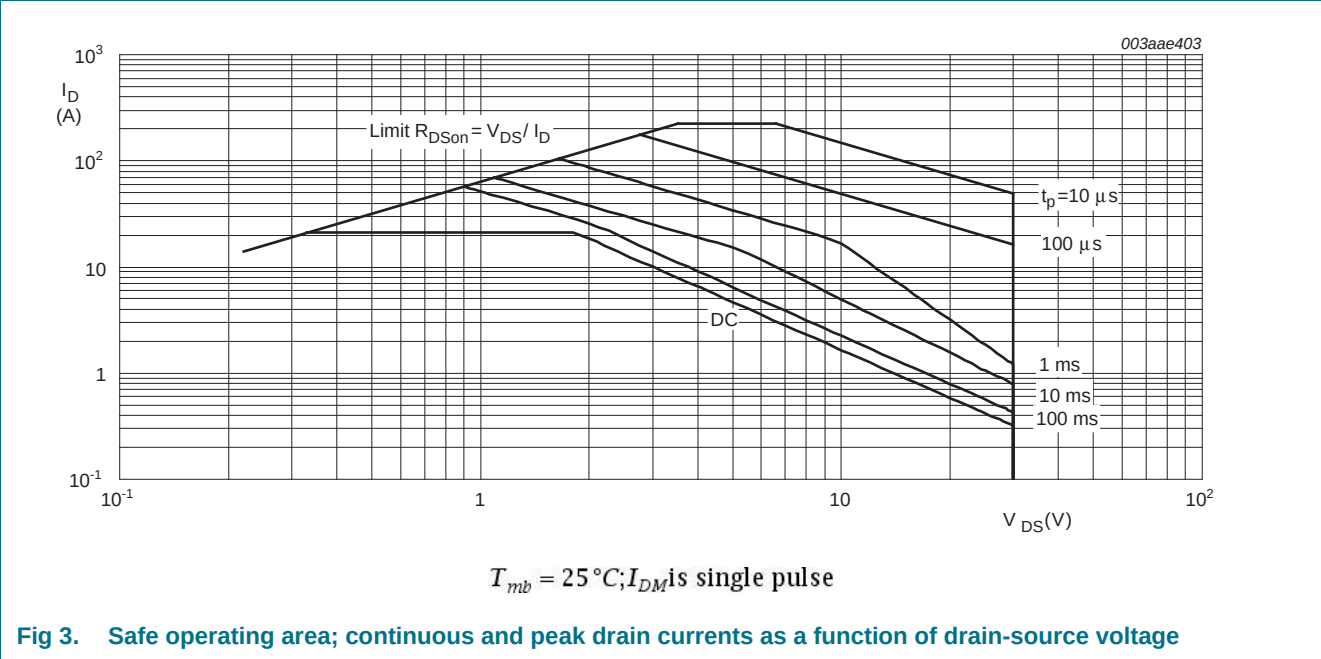
$V_{GS} \geq 10\text{ V}$; (1) Capped at 21 A due to wires.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of solder point temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1.9	4.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	[1]	-	55	60	K/W

[1] $R_{th(j-a)}$ is guaranteed by design and assumes that the device is mounted on a 40mm x 40mm x 70μm copper pad at 20°C ambient temperature. In practice $R_{th(j-a)}$ will be determined by the customer's PCB characteristics

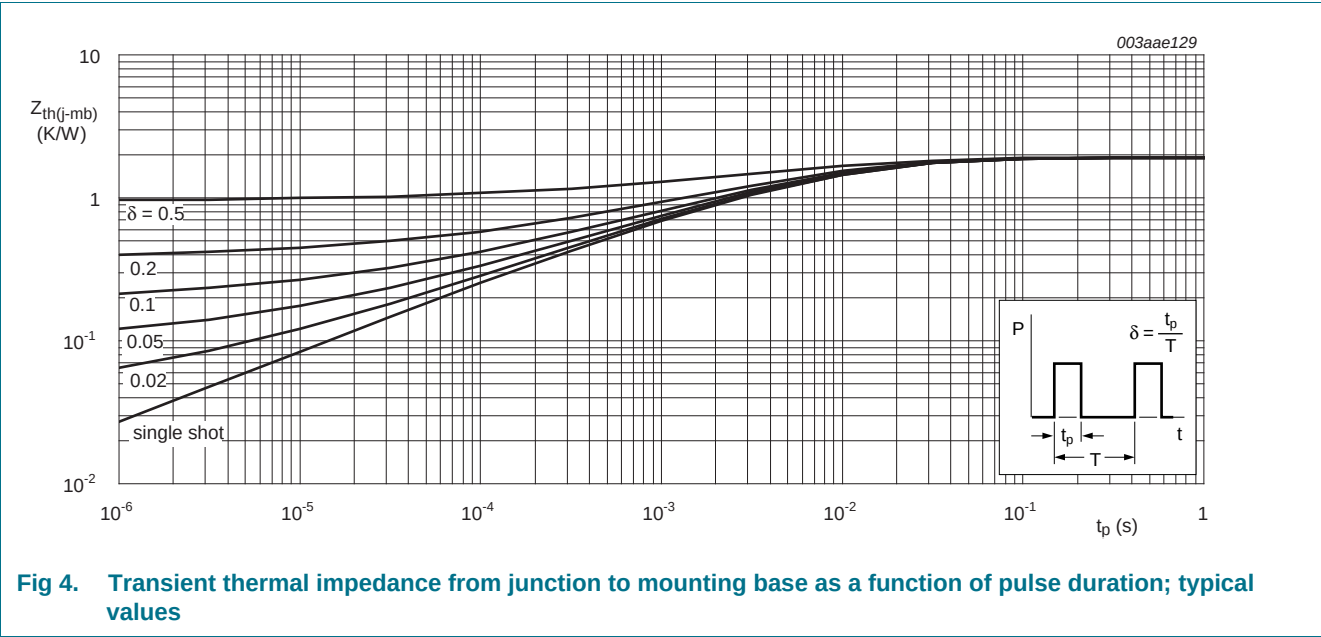


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^{\circ}\text{C}$	27	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^{\circ}\text{C};$ see Figure 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^{\circ}\text{C};$ see Figure 11 ; see Figure 10	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^{\circ}\text{C};$ see Figure 10	-	-	2.55	V
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	0.02	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^{\circ}\text{C}$	-	-	50	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	5	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	5	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C};$ see Figure 12	-	10.6	13	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^{\circ}\text{C};$ see Figure 13	-	-	11.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 150 \text{ }^{\circ}\text{C};$ see Figure 13	-	14.4	16.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C};$ see Figure 12	-	8	9	mΩ
R_G	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1.46	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 17	-	20.6	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 17 ; see Figure 14	-	10	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	18.6	-	nC
Q_{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	3.4	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.9	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.4	-	nC
Q_{GD}	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 17	-	2.9	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$ see Figure 14 ; see Figure 17	-	2.6	-	V
C_{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^{\circ}\text{C};$ see Figure 15	-	1193	-	pF
C_{oss}	output capacitance		-	223	-	pF
C_{rss}	reverse transfer capacitance		-	106	-	pF

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 1.5 Ω; V _{GS} = 10 V; R _{G(ext)} = 4.7 Ω; T _j = 25 °C	-	16	-	ns
t _r	rise time		-	18	-	ns
t _{d(off)}	turn-off delay time		-	22	-	ns
t _f	fall time		-	8	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 7.5 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 16	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 10 A; dI _S /dt = 100 A/μs;	-	30	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _{DS} = 15 V	-	22	-	nC

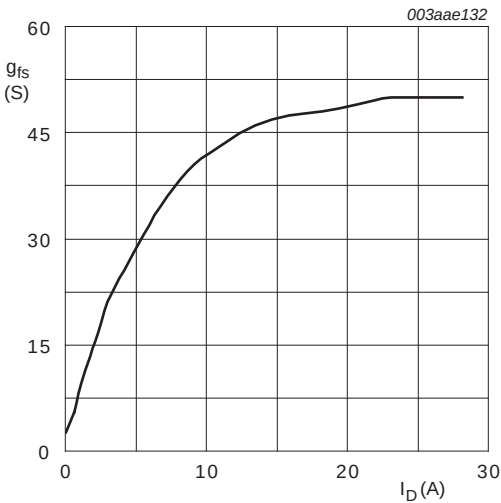


Fig 5. Forward transconductance as a function of drain current; typical values

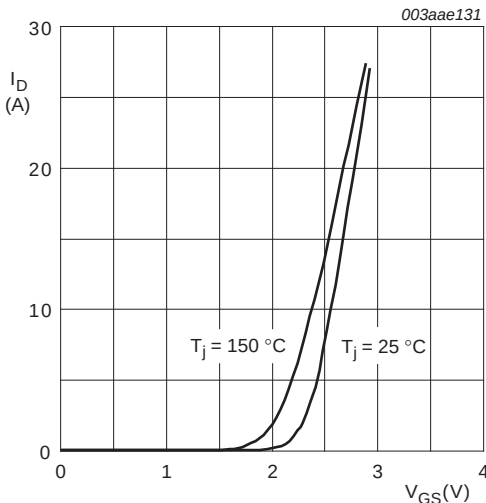
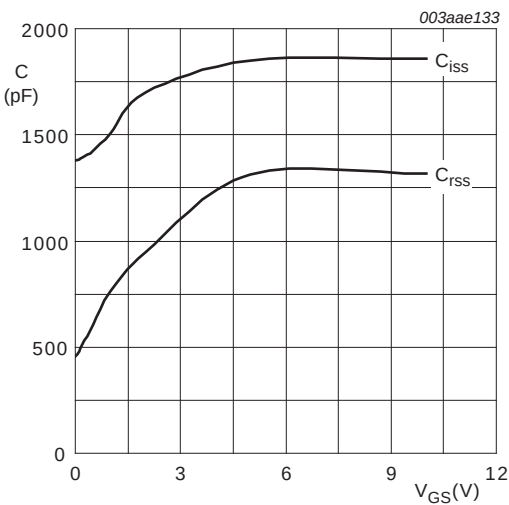
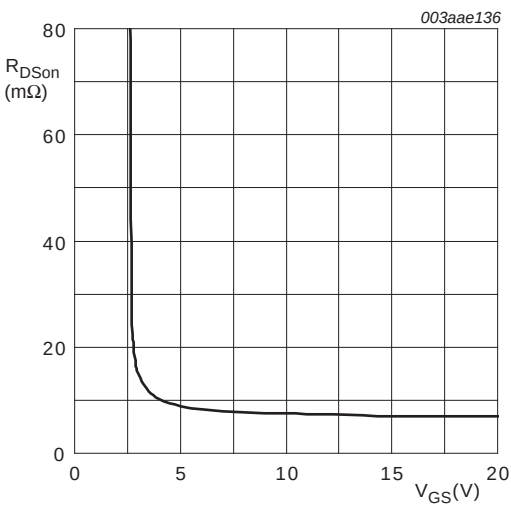


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



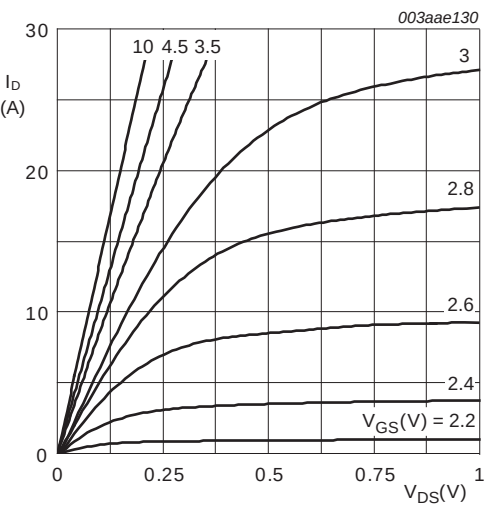
$V_{DS} = 0$ V; $f = 1$ MHz

Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage, typical values



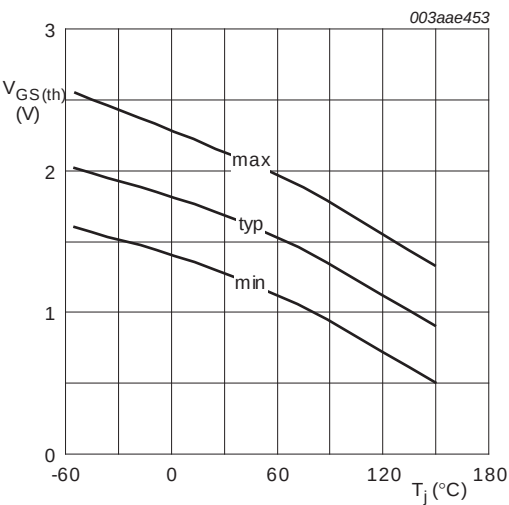
$T_j = 25$ °C; $I_D = 8$ A

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



$T_j = 25$ °C

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



$I_D = 1$ mA; $V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

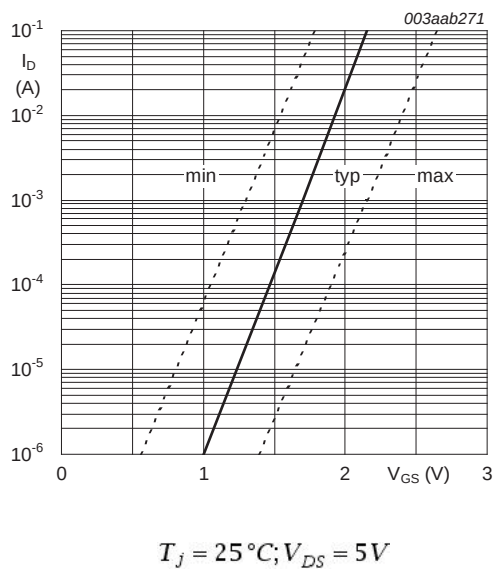


Fig 11. Sub-threshold drain current as a function of gate-source voltage

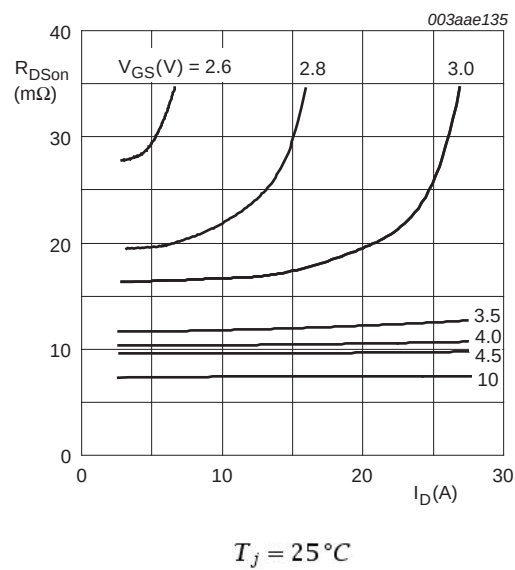


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

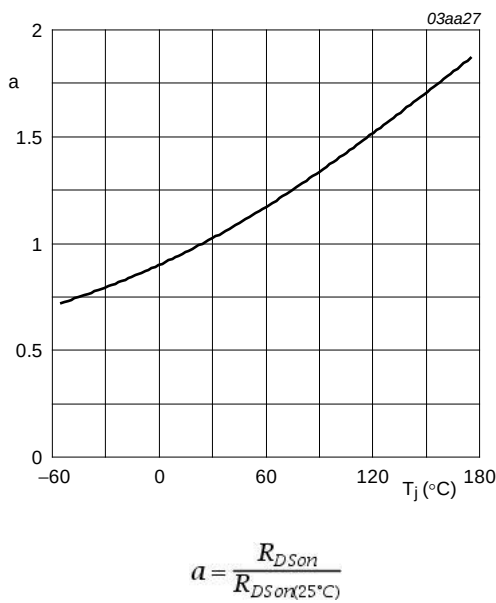


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

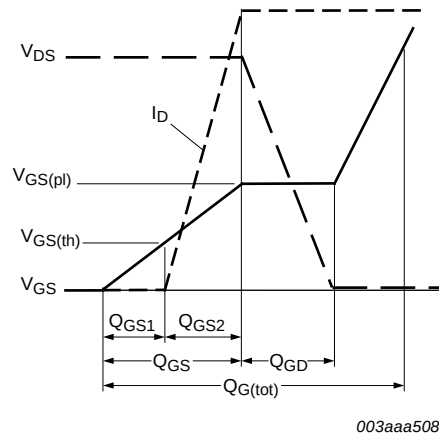


Fig 14. Gate charge waveform definitions

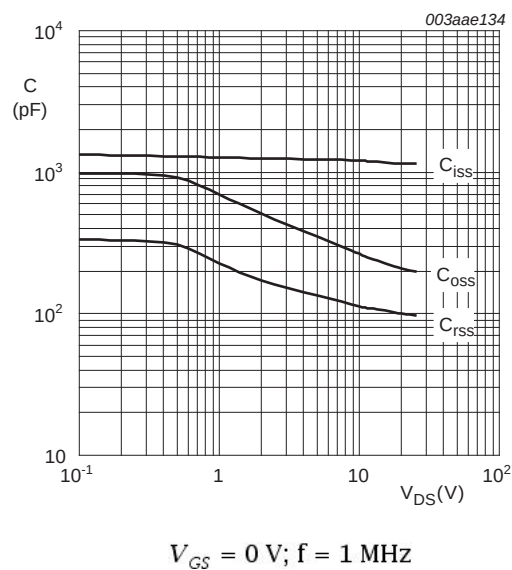


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

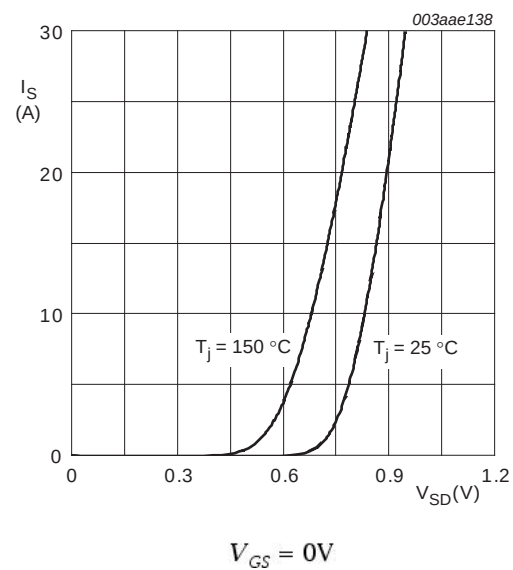


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

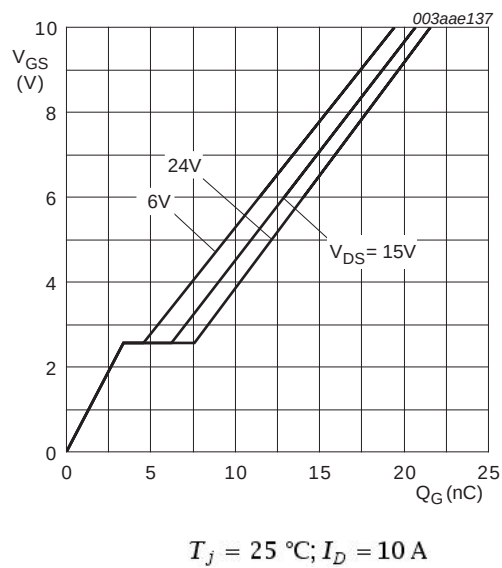


Fig 17. Gate-source voltage as a function of gate charge; typical values

7. Package outline

DFN3333-8: plastic thermal enhanced very thin small outline package; no leads;
8 terminals; body 3.3 x 3.3 x 1.0 mm

SOT873-1

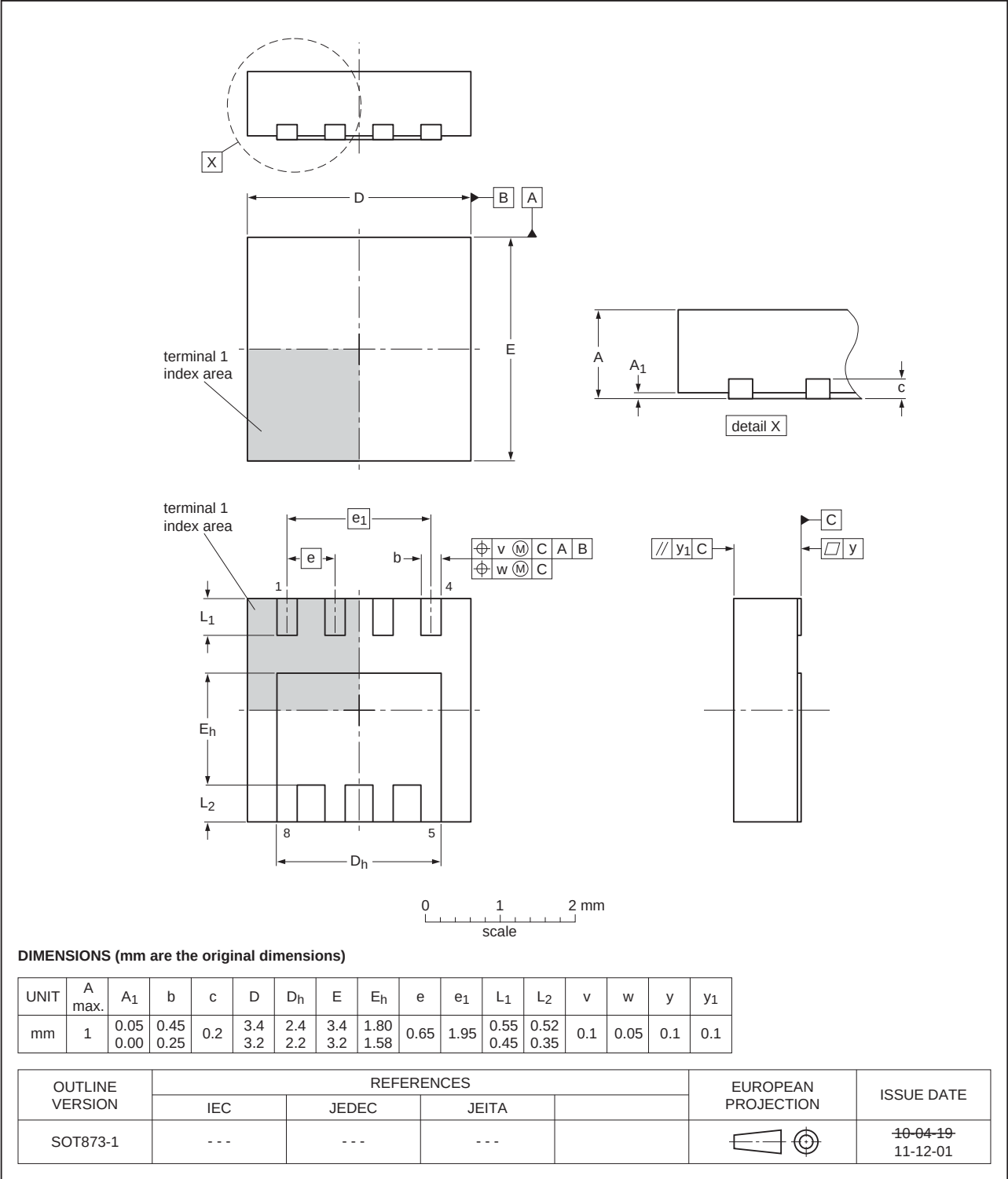


Fig 18. Package outline SOT873-1 (DFN3333-8)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R0-30LL v.5	20111213	Product data sheet	-	PSMN9R0-30LL v.4
Modifications:	• Various changes to content.			
PSMN9R0-30LL v.4	20100707	Product data sheet	-	PSMN9R0-30LL v.3

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

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